**HALOGEN** 

FREE





# P-Channel 1.8 V (G-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (mA)		
	1.2 at V <sub>GS</sub> = - 4.5 V	- 350		
- 20	1.6 at V <sub>GS</sub> = - 2.5 V	- 300		
	2.7 at V <sub>GS</sub> = - 1.8 V	- 150		

# SC-75A or SC-89

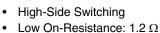
SC-75A (SOT-416): Si1013R - Marking Code D SC-89 (SOT-490): Si1013X - Marking Code B

#### **Ordering Information:**

Si1013R-T1-GE3 (SC-75A, Lead (Pb)-free and Halogen-free) Si1013X-T1-GE3 (SC-89, Lead (Pb)-free and Halogen-free)

#### **FEATURES**

 Halogen-free According to IEC 61249-2-21 Definition



Low Threshold: 0.8 V (Typ.)Fast Switching Speed: 14 ns

1.8 V Operation

TrenchFET<sup>®</sup> Power MOSFETs

• 2000 V ESD Protection

• Compliant to RoHS Directive 2002/95/EC

#### **APPLICATIONS**

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- · Battery Operated Systems
- Power Supply Converter Circuits
- · Load/Power Switching Cell Phones, Pagers

#### **BENEFITS**

- · Ease in Driving Switches
- · Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Low Battery Voltage Operation

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)					
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		$V_{DS}$	- 20		V
Gate-Source Voltage		$V_{GS}$	± 6		
Continuous Drain Current (T <sub>.I</sub> = 150 °C) <sup>b</sup>	T <sub>A</sub> = 25 °C	I <sub>D</sub>	- 400	- 350	A
Continuous Drain Current (1 <sub>J</sub> = 150 °C)	T <sub>A</sub> = 85 °C		- 300	- 275	
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	- 1000		mA
Continuous Source Current (Diode Conduction) <sup>b</sup>		I <sub>S</sub>	- 275	- 250	
Mariana Baran Biraira Kada 100 75	T <sub>A</sub> = 25 °C	P <sub>D</sub>	175	150	mW
Maximum Power Dissipation <sup>b</sup> for SC-75	T <sub>A</sub> = 85 °C		90	80	
Mariana Barra Biraira tirah (a. 00.00	T <sub>A</sub> = 25 °C		275	250	
Maximum Power Dissipation <sup>b</sup> for SC-89	T <sub>A</sub> = 85 °C		160	140	
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	
Gate-Source ESD Rating (HBM, Method 3015)		ESD	2000		V

#### Notes

- a. Pulse width limited by maximum junction temperature.
- b. Surface mounted on FR4 board.

Document Number: 71167 S10-2432-Rev. D, 25-Oct-10

# Vishay Siliconix



SPECIFICATIONS (T <sub>A</sub> =		·		_			
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 0.45			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$		± 1	± 2	μΑ	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 16 V, V <sub>GS</sub> = 0 V		- 0.3	- 100	nA	
		V <sub>DS</sub> = - 16 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 85 °C			- 5	μΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = - 5 V, V <sub>GS</sub> = - 4.5 V	- 700			mA	
Davis Occurs On Otata	R <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, I_D = -350 \text{ mA}$		0.8	1.2	Ω	
Drain-Source On-State Resistance <sup>a</sup>		$V_{GS} = -2.5 \text{ V}, I_D = -300 \text{ mA}$		1.2	1.6		
		V <sub>GS</sub> = - 1.8 V, I <sub>D</sub> = - 150 mA		1.8	2.7		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = - 10 V, I <sub>D</sub> = - 250 mA		0.4		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = - 150 mA, V <sub>GS</sub> = 0 V		- 0.8	- 1.2	V	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_g$			1500			
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -250 \text{ mA}$		150		рС	
Gate-Drain Charge	$Q_{gd}$			450		1	
Turn-On Delay Time	t <sub>d(on)</sub>			5			
Rise Time	t <sub>r</sub>	$V_{DD}$ = - 10 V, $R_L$ = 47 $\Omega$		9		1	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong$ - 200 mA, $V_{GEN}$ = - 4.5 V, $R_g$ = 10 $\Omega$		35		ns	
Fall Time	t <sub>f</sub>			11		1	

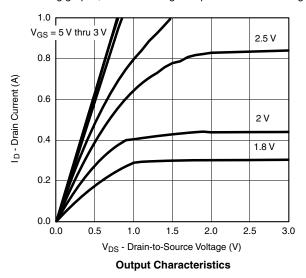
#### Notes:

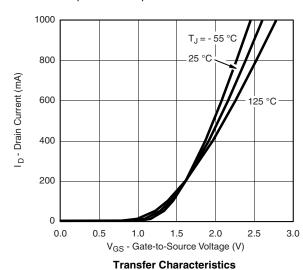
- a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

For the following graphs, P-Channel negative polarities for all voltage and current values are represented as positive values.



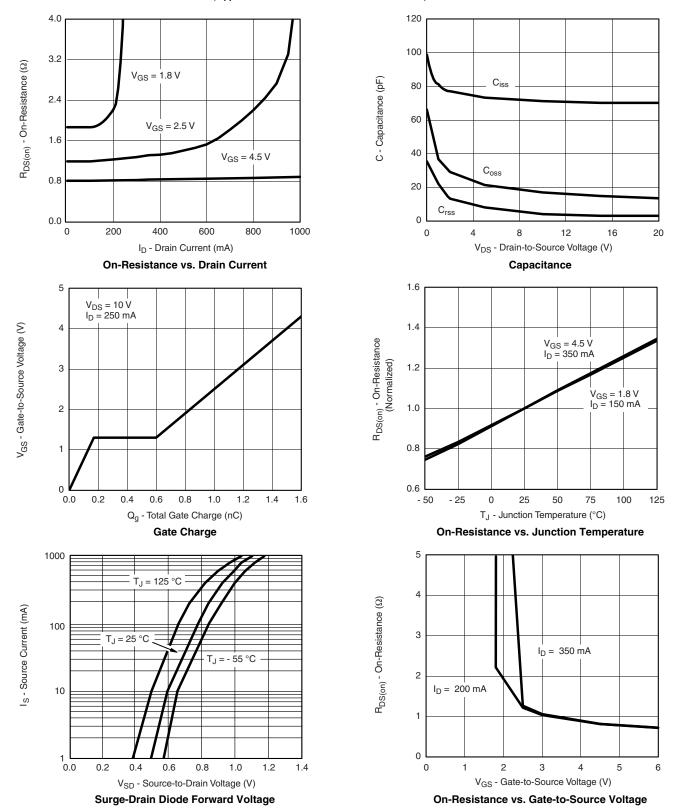








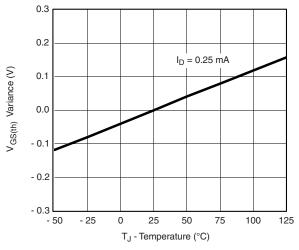
# TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)

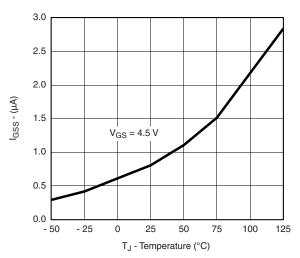


# Vishay Siliconix

# VISHAY

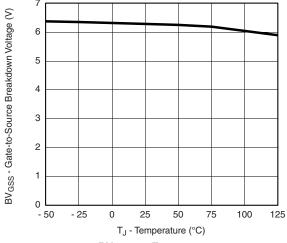
# **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

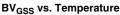


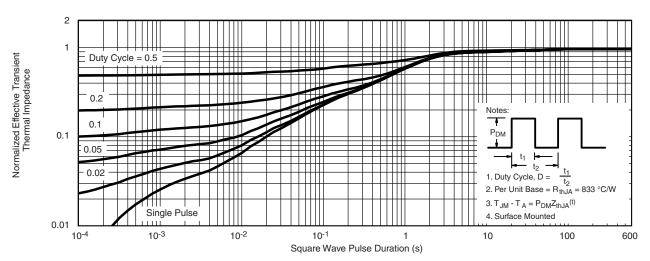


Threshold Voltage Variance vs. Temperature







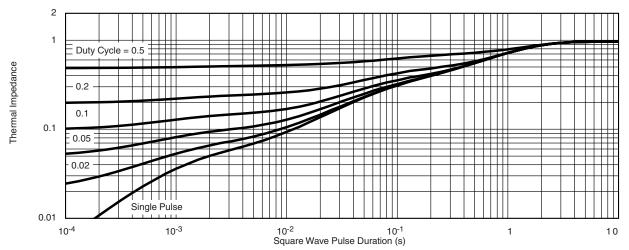


Normalized Thermal Transient Impedance, Junction-to-Ambient (SC-75A)





# **TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)

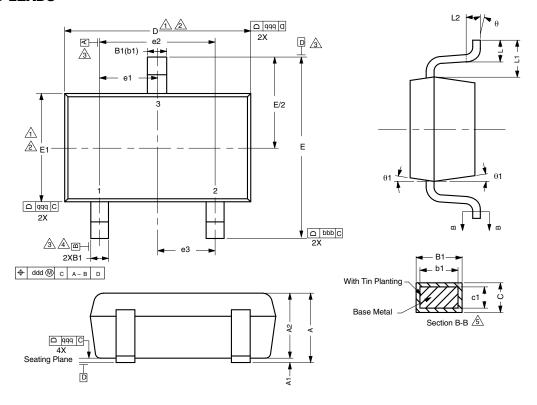


Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?71167">www.vishay.com/ppg?71167</a>.



#### SC-75A: 3-LEADS



#### **Notes**

Dimensions in millimeters will govern.

Dimension D does not include mold flash, protrusions or gate burrs. Mold flash protrusions or gate burrs shall not exceed 0.10 mm per end. Dimension E1 does not include Interlead flash or protrusion. Interlead flash or protrusion shall not exceed 0.10 mm per side.

Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, tie bar burrs, gate burrs and interelead flash, but including any mismatch between the top and bottom of the plastic body.

2) Datums A, B and D to be determined 0.10 mm from the lead tip.

4. Terminal positions are shown for reference only.

These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

DIMENSIONS	TOLERANCES		
aaa	0.10		
bbb	0.10		
ccc	0.10		
ddd	0.10		

	MILLIMETERS				
DIM.	MIN.	NOM.	MAX.	NOTE	
Α	-	-	0.80		
A <sub>1</sub>	0.00	-	0.10		
A <sub>2</sub>	0.65	0.70	0.80		
B <sub>1</sub>	0.19	-	0.24	5	
b <sub>1</sub>	0.17	-	0.21		
С	0.13	-	0.15	5	
C <sub>1</sub>	0.10	-	0.12	5	
D	1.48	1.575	1.68	1, 2	
Е	1.50	1.60	1.70		
E <sub>1</sub>	0.66	0.76	0.86	1, 2	
e <sub>1</sub>		0.50 BSC			
e <sub>2</sub>		1.00 BSC			
e <sub>3</sub>		0.50 BSC			
L	0.15	0.205	0.30		
L <sub>1</sub>	0.40 REF				
L <sub>2</sub>	0.15 BSC				
θ	0°	-	8°		
$\theta_1$	4°	-	10°		
ECN: E11-	2210-Rev. D.	08-Aug-11			

ECN: E11-2210-Rev. D, 08-Aug-11

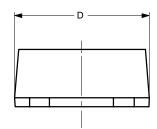
DWG: 5868

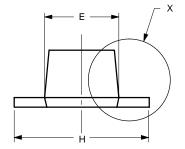


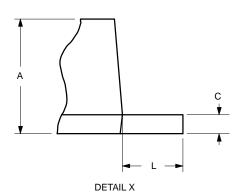


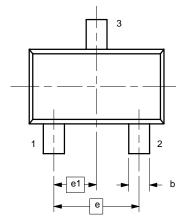
# Vishay Siliconix

### SC89-3









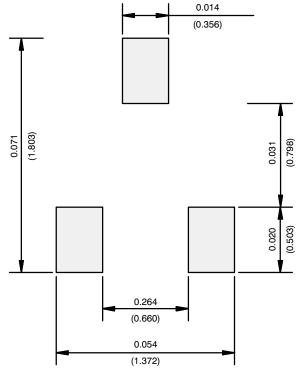
**MILLIMETERS INCHES** Dim Min Max Min Max 0.60 0.024 0.031 Α 0.80 0.23 0.33 0.009 0.013 b С 0.10 0.004 0.008 0.20 0.067 D 1.50 1.70 0.059 Ε 0.75 0.95 0.030 0.037 1.00 BSC 0.040 BSC е 0.50 BSC 0.020 BSC e<sub>1</sub> Н 1.50 0.059 0.067 0.30 0.012 0.020 0.50

ECN: S-03946—Rev. B, 09-Jul-01 DWG: 5869

Document Number: 71377 www.vishay.com 06-Jul-01



### **RECOMMENDED MINIMUM PADS FOR SC-75A: 3-Lead**



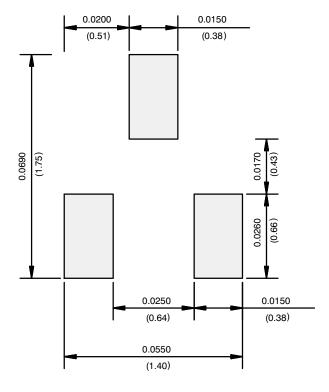
Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

APPLICATION NOTE



### **RECOMMENDED MINIMUM PADS FOR SC-89: 3-Lead**



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



# **Legal Disclaimer Notice**

Vishay

# **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

# **Material Category Policy**

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.